FAIRCI SEMICOND			October 1987 Revised January 1999
General Do The MM74C14 H mentary MOS (C N- and P-channe and negative goi low variation with	mitt Trigge escription MOS) integrated circuit el enhancement transis g threshold voltages V respect to temperature	nonolithic comple- t constructed with stors. The positive T_+ and V_{T-} , show e (typ. 0.0005V/°C	All inputs are protected from damage due to static dis- charge by diode clamps to V _{CC} and GND. Features Wide supply voltage range: 3.0V to 15V High noise immunity: 0.70 V _{CC} (typ.)
anteed.	d hysteresis, V _{T+} – V _{T-}	≥ 0.2 V _{CC} is guar-	 Low power: TTL compatibility: 0.4 V_{CC} (typ.) 0.2 V_{CC} guaranteed Hysteresis: 0.4 V_{CC} (typ.): 0.2 V_{CC} guaranteed
Ordering (
Order Number MM74C14M	Package Number M14A 14	4-Lead Small Outline	Package Description Integrated Circuit (SOIC), JEDEC MS-120, 0.150" Narrow
MM74C14N			-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
	V	Pin Assignments f	or DIP and SOIC
lec		Pin Assignments f	

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Absolute Maximum Ratings(Note 1)

Voltage at Any Pin Operating Temperature Range Storage Temperature Range Power Dissipation Dual-In-Line Small Outline Operating V_{CC} Range

-0.3Vto V_{CC} + 0.3V -40°C to +85°C -65°C to +150°C 700 mW 500mW 3.0V to 15V

Absolute Maximum V_{CC} Lead Temperature (Soldering, 10 seconds)

18V

260°C

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Tempera-ture Range" they are not meant to imply that the devices should be oper-ated at these limits. The Electrical Characteristics tables provide conditions for actual device operation.

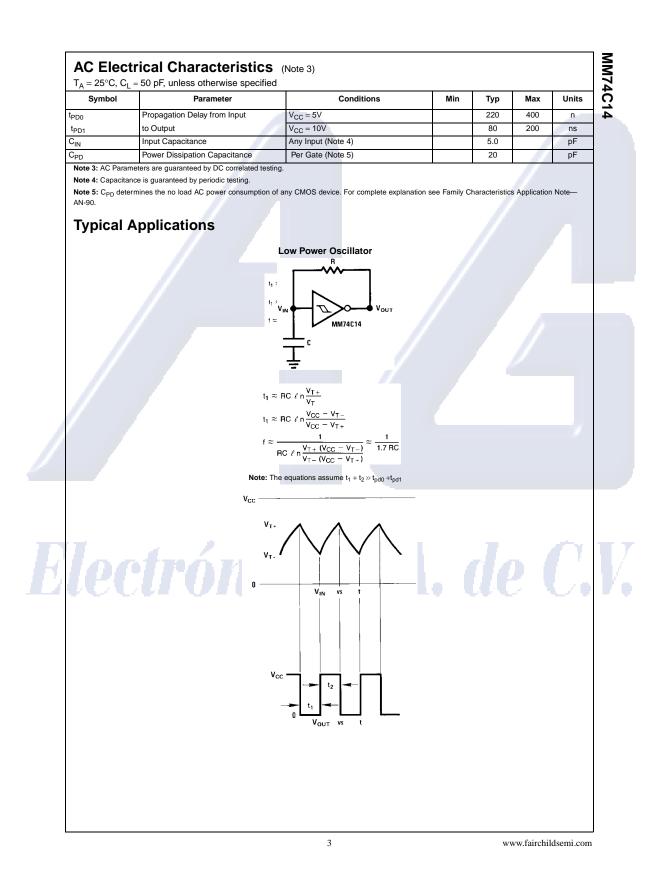
DC Electrical Characteristics

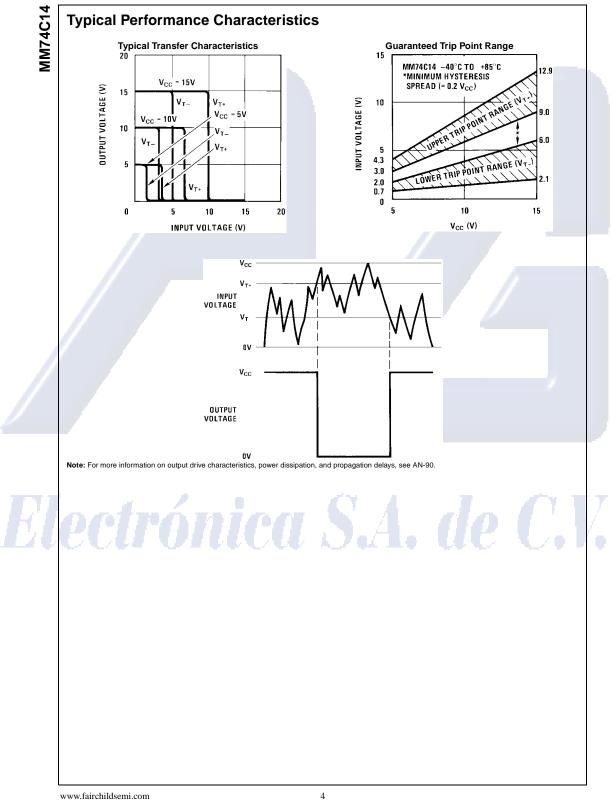
Symbol	Parameter	Conditions	Min	Тур	Max	Units
CMOS TO C	Mos		11	1 1	7	1
V _{T+}	Positive Going Threshold Voltage	$V_{CC} = 5V$	3.0	3.6	4.3	V
		$V_{CC} = 10V$	6.0	6.8	8.6	V
		$V_{CC} = 15V$	9.0	10.0	12.9	V
V _{T-}	Negative Going Threshold Voltage	$V_{CC} = 5V$	0.7	1.4	2.0	V
		$V_{CC} = 10V$	1.4	3.2	4.0	V
		V _{CC} = 15V	2.1	5.0	6.0	V
V _{T+} -V _{T-}	Hysteresis	$V_{CC} = 5V$	1.0	2.2	3.6	V
		$V_{CC} = 10V$	2.0	3.6	7.2	V
		V _{CC} = 15V	3.0	5.0	10.8	V
V _{OUT(1)}	Logical "1" Output Voltage	$V_{CC} = 5V, I_{O} = -10 \ \mu A$	4.5			V
	1	$V_{CC} = 10V, I_{O} = -10 \mu A$	9.0			V
V _{OUT(0)}	Logical "0" Output Voltage	$V_{CC} = 5V, I_{O} = 10 \ \mu A$			0.5	V
		$V_{CC} = 10V, I_{O} = 10 \ \mu A$			1.0	V
I _{IN(1)}	Logical "1" Input Current	$V_{CC} = 15V, V_{IN} = 15V$		0.005	1.0	μΑ
I _{IN(0)}	Logical "0" Input Current	$V_{CC} = 15V, V_{IN} = 0V$	-1.0	-0.005		μΑ
I _{CC}	Supply Current	$V_{CC} = 15V, V_{IN} = 0V/15V$		0.05	15	μΑ
		V _{CC} = 5V, V _{IN} = 2.5V (Note 2)		20		μΑ
		V _{CC} = 10V, V _{IN} = 5V (Note 2)		200		μΑ
		V _{CC} = 15V, V _{IN} = 7.5V (Note 2)		600		μΑ
CMOS/LPTT	LINTERFACE					
V _{IN(1)}	Logical "1" Input Voltage	$V_{CC} = 5V$	4.3			V
V _{IN(0)}	Logical "0" Input Voltage	$V_{CC} = 5V$			0.7	V
V _{OUT(1)}	Logical "1" Output Voltage	74C, V_{CC} = 4.75V, I_{O} = -360 μ A	2.4			V
V _{OUT(0)}	Logical "0" Output Voltage	74C, V _{CC} = 4.75V, I _O = 360 μA			0.4	V

OUTPUT DRIVE (see Family Characteristics Data Sheet) $T_A = 25^{\circ}C$ (Short Circuit Current)

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ISOURCE	Output Source Current	$V_{CC} = 5V, V_{OUT} = 0V$	-1.75	-3.3	mA	
	(P-Channel)					
ISOURCE	Output Source Current	$V_{CC} = 10V, V_{OUT} = 0V$	-8.0	-15	mA	
	(P-Channel)					
I _{SINK}	Output Sink Current	$V_{CC} = 5V, V_{OUT} = V_{CC}$	1.75	3.6	mA	
	(N-Channel)					
I _{SINK}	Output Sink Current	$V_{CC} = 10V, V_{OUT} = V_{CC}$	8.0	16	mA	
	(N-Channel)					
Note 2: Only one of the six inputs is at $\frac{1}{2}$ V _{CC} the others are either at V _{CC} or GND.						

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